Vishay Semiconductors

## Thyristor High Voltage, Phase Control SCR, 40 A



PRIMARY CHARACTERISTICS				
I <sub>T(AV)</sub>	35 A			
V <sub>DRM</sub> /V <sub>RRM</sub>	1200 V			
$V_{TM}$	1.45 V			
I <sub>GT</sub>	150 mA			
$T_J$	-40 °C to +125 °C			
Package	TO-247AD 3L			
Circuit configuration	Single SCR			

#### **FEATURES**

- Low I<sub>GT</sub> parts available
- Designed and qualified according to JEDEC® - JESD 47



- Flexible solution for reliable AC power rectification
- Easy control peak current at charger power up to reduce passive / electromechanical components
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>

#### **APPLICATIONS**

 Typical usage is in input rectification crowbar (soft start) and AC switch in motor control, UPS, welding and battery charge

### **DESCRIPTION**

The VS-40TPS12.. high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications.

AEC-Q101 qualified P/N available (VS-40TPS12LHM3, VS-40TPS12ALHM3).

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
I <sub>T(AV)</sub>	Sinusoidal waveform	35	A		
I <sub>RMS</sub>		55	^		
V <sub>RRM</sub> /V <sub>DRM</sub>		1200	V		
I <sub>TSM</sub>		600	А		
$V_{T}$	40 A, T <sub>J</sub> = 25 °C	1.45	V		
dv/dt		1000	V/µs		
di/dt		100	A/µs		
T <sub>J</sub>		-40 to +125	°C		

VOLTAGE RATINGS			
PART NUMBER	V <sub>RRM</sub> /V <sub>DRM</sub> , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I <sub>RRM</sub> /I <sub>DRM</sub> AT 125 °C mA
VS-40TPS12AL-M3	1200	1300	10
VS-40TPS12L-M3	1200	1300	] 10



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ABSOLUTE MAXIMUM RATINGS	}				
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum average on-state current	I <sub>T(AV)</sub>	T <sub>C</sub> = 79 °C, 180° conduction half sine wave	Э	35	
Maximum continuous RMS on-state current as AC switch	I <sub>T(RMS)</sub>			55	А
Maximum peak, one-cycle		10 ms sine pulse, rated V <sub>RRM</sub> applied		500	
non-repetitive surge current	I <sub>TSM</sub>	10 ms sine pulse, no voltage reapplied	ladial	600	
Maximum I <sup>2</sup> t for fusing	I <sup>2</sup> t	10 ms sine pulse, rated V <sub>RRM</sub> applied	Initial $T_{.1} = T_{.1} \text{ max.}$	1250	A <sup>2</sup> s
Maximum I-t for fusing	1-1	10 ms sine pulse, no voltage reapplied	ij – ijiliax.	1760	A-S
Maximum I <sup>2</sup> √t for fusing	I <sup>2</sup> √t	t = 0.1 ms to 10 ms, no voltage reapplied		17 600	A²√s
Low level value of threshold voltage	V <sub>T(TO)1</sub>		1.02	V	
High level value of threshold voltage	V <sub>T(TO)2</sub>	T 105 °C	1.23	v	
Low level value of on-state slope resistance	r <sub>t1</sub>	T <sub>J</sub> = 125 °C	9.74	m0	
High level value of on-state slope resistance	r <sub>t2</sub>		7.50	mΩ	
Maximum peak on-state voltage	$V_{TM}$	110 A, T <sub>J</sub> = 25 °C		1.85	V
Maximum rate of rise of turned-on current	di/dt	T <sub>J</sub> = 25 °C		100	A/µs
Maximum holding current	I <sub>H</sub>	Anode supply = $6 \text{ V}$ , resistive load, initial $T_J$	= 1 A, I <sub>T</sub> = 25 °C	300	
Maximum latching current	ΙL	Anode supply = 6 V, resistive load, $T_J = 25$	°C	350	т Л
Marrian was a sound alive at leading a summer		T <sub>J</sub> = 25 °C	25 °C		mA
Maximum reverse and direct leakage current	I <sub>RRM/</sub> I <sub>DRM</sub>	$V_R = \text{rated } V_{RRM}/V_{DR}$	RM	10	1
Maximum rate of rise of off-state voltage 40TPS12A	dv/dt	$T_J = T_J$ maximum, linear to 80 % $V_{DRM},R_g$ - $k$ = 100 $\Omega$		500	V/uo
Maximum rate of rise of off-state voltage 40TPS12	αν/ατ			1000 V/	V/µs

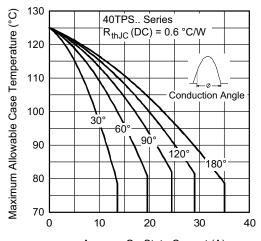
TRIGGERING					
PARAMETER	SYMBOL	TEST CO	NDITIONS	VALUES	UNITS
Maximum peak gate power	P <sub>GM</sub>				W
Maximum average gate power	P <sub>G(AV)</sub>			2.5	VV
Maximum peak gate current	I <sub>GM</sub>			2.5	Α
Maximum peak negative gate voltage	-V <sub>GM</sub>			10	V
		T <sub>J</sub> = -40 °C	Anada sunah. CV	2.0	
Maximum required DC gate voltage to trigger	$V_{GT}$	T <sub>J</sub> = 25 °C	Anode supply = 6 V	1.7	V
		T <sub>J</sub> = 125 °C	Tesistive load	1.3	
		T <sub>J</sub> = -40 °C	Anode supply = 6 V resistive load	200	
Maximum required DC gate current to trigger	I <sub>GT</sub>	T <sub>J</sub> = 25 °C		150	mA
Maximum required DC gate current to trigger		T <sub>J</sub> = 125 °C		80	
		$T_J = 25$ °C, for 40TPS12A		40	
Maximum DC gate voltage not to trigger for 40TPS12	$V_{GD}$	T <sub>J</sub> = 125 °C, V <sub>DRM</sub> = rated value		0.25	٧
Maximum DC gate current not to trigger for 40TPS12	I <sub>GD</sub>			6	mA
Maximum DC gate voltage not to trigger for 40TPS12A	$V_{GD}$	T <sub>J</sub> = 125 °C, V <sub>DRM</sub> = rated value		0.15	V
Maximum DC gate current not to trigger for 40TPS12A	I <sub>GD</sub>			1	mA



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THERMAL AND MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum junction and storage temperature range	e T <sub>J</sub> , T <sub>Stg</sub>		-40 to +125	°C			
Maximum thermal resistance, junction to case	R <sub>thJC</sub>	DC appration	0.6				
Maximum thermal resistance, junction to ambient	R <sub>thJA</sub>	DC operation	40	°C/W			
Maximum thermal resistance, case to heat sink	R <sub>thCS</sub>	Mounting surface, smooth and greased	0.25				
Approximate weight			6	g			
Approximate weight			0.21	oz.			
Mounting torque minimur	m		6 (5)	kgf · cm			
maximur	n		12 (10)	(lbf·in)			
Marking device		Case style TO-247AD 3L	40TPS12AL				
iviarking device		Case style 10-247AD 3L	40TPS12L				



Average On-State Current (A) Fig. 1 - Current Rating Characteristics

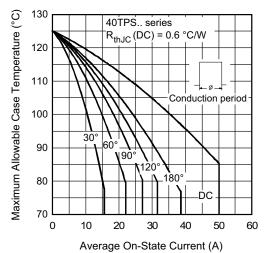


Fig. 2 - Current Rating Characteristics

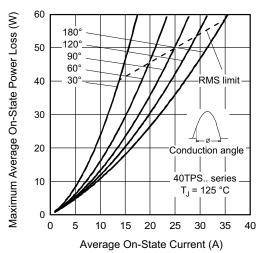


Fig. 3 - On-State Power Loss Characteristics

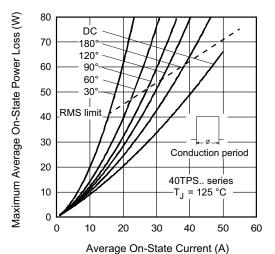


Fig. 4 - On-State Power Loss Characteristics

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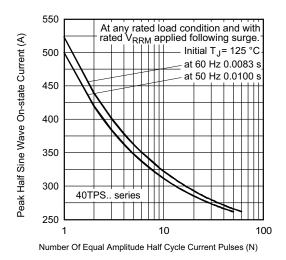


Fig. 5 - Maximum Non-Repetitive Surge Current

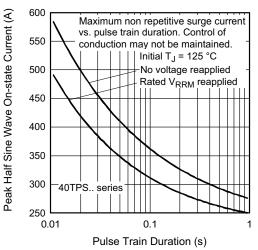
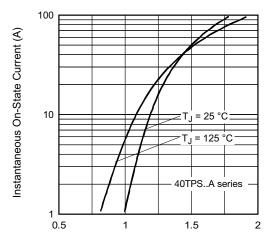
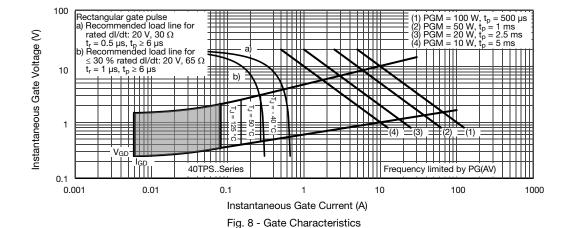


Fig. 6 - Maximum Non-Repetitive Surge Current



Instantaneous On-State Voltage (V)
Fig. 7 - On-State Voltage Drop Characteristics



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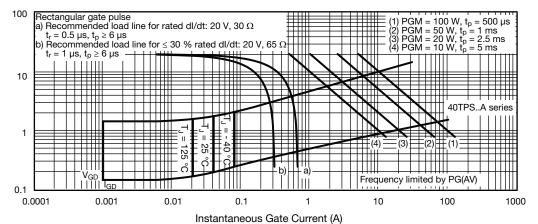


Fig. 9 - Gate Characteristics

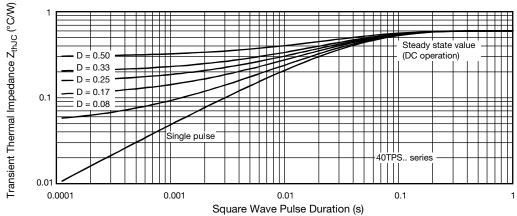


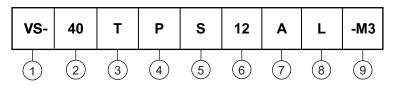
Fig. 10 - Thermal Impedance  $Z_{thJC}$  Characteristics

12 = 1200 V

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### **ORDERING INFORMATION TABLE**

Device code



1 - Vishay Semiconductors product

2 - Current rating (40 = 40 A)

3 - Circuit configuration:

T = thyristor

4 - Package:

P = TO-247

5 - Type of silicon:

S = standard recovery rectifier

6 - Voltage ratings

• A = Low lgt selection 40 mA maximum

• None = standard lgt selection

8 - L = long leads

9 - Environmental digit:

-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)					
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION		
VS-40TPS12AL-M3	25	500	Antistatic plastic tubes		
VS-40TPS12L-M3	25	500	Antistatic plastic tubes		

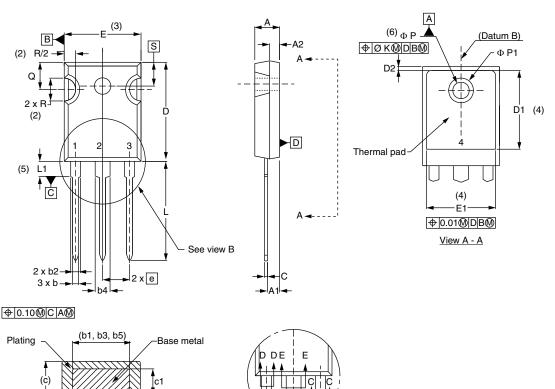
LINKS TO RELATED DOCUMENTS			
Dimensions	TO-247AD 3L	www.vishay.com/doc?95626	
Part marking information	TO-247AD 3L	www.vishay.com/doc?95007	



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## **TO-247AD 3L**

#### **DIMENSIONS** in millimeters and inches



(4) Section C - C, D - D, E - E							
SYMBOL	MILLIN	IETERS	INC	HES	NOTES		
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES		
Α	4.65	5.31	0.183	0.209			
A1	2.21	2.59	0.087	0.102			
A2	1.50	2.49	0.059	0.098			
b	0.99	1.40	0.039	0.055			

0.039

0.065

0.065

0.102

0.102

0.015

0.015

0.776

0.515

0.053

0.094

0.092

0.135

0.133

0.035

0.033

0.815

(h h2 h4)

:5	

View B

SYMBOL	IVIILLIIV	ILILING	INOTIES		NOTES
	MIN.	MAX.	MIN.	MAX.	NOTES
D2	0.51	1.30	0.020	0.051	
E	15.29	15.87	0.602	0.625	3
E1	13.46	-	0.53	-	
е	5.46	BSC	0.215	BSC	
ØΚ	0.2	254	0.0	10	
L	19.81	20.32	0.780	0.800	
L1	3.71	4.29	0.146	0.169	
ØΡ	3.56	3.66	0.14	0.144	
Ø P1	-	6.98	-	0.275	
Q	5.31	5.69	0.209	0.224	
R	4.52	5.49	0.178	0.216	
S	5.51	BSC	0.217	BSC	
•	•		•		•

INCHES

MILLIMETERS

### Notes

b1

b2

b3

b4

b5

С

с1

D

D1

(1) Dimensioning and tolerancing per ASME Y14.5M-1994

1.35

2.39

2.34

3.43

3.38

0.89

0.84

20.70

- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. These dimensions are measured at the outermost extremes of the plastic body

3

- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1

0.99

1.65

1.65

2.59

2.59

0.38

0.38

19.71

13.08

- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC® outline TO-247 with exception of dimension A min., D, E min., Q min., S, and note 4



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